

# MOS Memory Data Book

1986

**Commercial and Military  
Specifications**



**TEXAS  
INSTRUMENTS**

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Specifications contained in this data book supersede all data for these products published by TI in the United States before November 1985.

## INTRODUCTION

The 1986 MOS Memory Data Book from Texas Instruments includes complete detailed specifications on the expanding MOS Memory product line including Dynamic Random-Access Memories (DRAMs), Single-In-Line Package DRAM Memory Modules (SIPs), Erasable Programmable Read-Only Memories (EPROMs), MOS one-time Programmable Read-Only Memories (PROMs), and Read-Only Memories (ROMs) for the United States market. Also provided are military specifications for the DRAM product line. This is TI's first MOS Memory data book to include specifications for complementary MOS (CMOS) memory devices (which now span all MOS Memory product lines). Surface-mount packaging is now available on all 64K, 256K and 1 MEG DRAMs and CMOS ROMs. Another packaging option for DRAMs is the SIP which can increase memory density by over 3.5 times that of dual-in-line packages.

This data book is divided into 12 sections. Section 1, General Information, includes the table of contents, an alphanumeric index for quickly finding device numbers, plus a device selection guide and a product reference guide for quick overview of the broad TI MOS Memory product line. Page numbers are included on the product reference guide for easy access to the detailed specifications. In Section 2, the Interchangeability Guide lists alternate vendor part numbering examples in addition to alternate sources to TI devices (based on published data). Product specifications for 71 devices can be found in Sections 4 through 8.

Recently published design considerations, product applications, and technical articles can be found in Section 9. Also included is a section (Section 12) on guidelines for handling ESD sensitive devices, since all MOS Memory devices are ESD sensitive.

The data sheets within each section are in alphanumeric order; Product Preview information is included at the end of the section. Data Sheets listed with a "TMX" prefix and Product Preview disclaimer include target specifications for products that are currently under development at TI. The inclusion of these specifications does not imply that these products are or will be in production, or will meet these parameters.

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